

Product Summary

| $V_{(BR)DSS}$ | $R_{DS(ON)}$ | I_D $T_A = 25^\circ C$ |
|---------------|-----------------------|-----------------------------|
| 60V | 3.0Ω @ $V_{GS} = 10V$ | 400mA |
| | 4.0Ω @ $V_{GS} = 5V$ | 330mA |

Description and Applications

These N-Channel enhancement mode field effect transistors are produced using DIODES proprietary, high density, uses advanced trench technology. These products have been designed to minimize on-state resistance while provide rugged, reliable, and fast switching performance. These products are particularly suited for low voltage, low current applications such as small

- Load switching

Features and Benefits

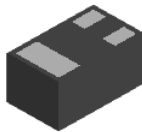
- N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- **ESD Protected Gate, 1.2kV HBM**
- **Lead, Halogen and Antimony Free, RoHS Compliant**
- **"Green" Device (Notes 1 and 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

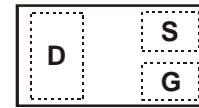
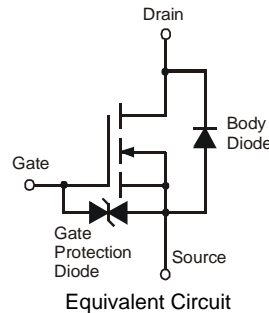
- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.001 grams (approximate)



X1-DFN1006-3



Bottom View



Top View
Pin Configuration

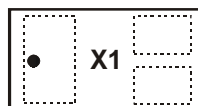
Ordering Information (Note 3)

| Part Number | Case | Packaging |
|---------------|--------------|--------------------|
| DMN65D8LFB-7 | X1-DFN1006-3 | 3,000/Tape & Reel |
| DMN65D8LFB-7B | X1-DFN1006-3 | 10,000/Tape & Reel |

- Notes:
1. No purposefully added lead. Halogen and Antimony Free.
 2. Diodes Inc.'s "Green" Policy can be found on our website at <http://www.diodes.com>
 3. For packaging details, go to our website at <http://www.diodes.com>

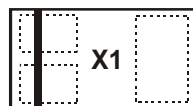
Marking Information

DMN65D8LFB-7



Top View
Dot Denotes Drain Side

DMN65D8LFB-7B



Top View
Bar Denotes Gate and Source Side

X1 = Product Type Marking Code

ate Code Key

| Year | 2011 | 2012 | 2013 | 2014 | 2015 | 2016 | 2017 |
|------|------|------|------|------|------|------|------|
| Code | Y | Z | A | B | C | D | E |

| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
|-------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | O | N | D |

Maximum Ratings

| Characteristic | | | Symbol | Value | Units |
|--|--------------|--------------------|-----------|----------|-------|
| Drain-Source Voltage | | | V_{DSS} | 60 | V |
| Gate-Source Voltage | | | V_{GSS} | ± 20 | V |
| Continuous Drain Current (Note 4) $V_{GS} = 10V$ | Steady State | $T_A = 25^\circ C$ | I_D | 260 | mA |
| | | $T_A = 70^\circ C$ | | 210 | |
| Continuous Drain Current (Note 5) $V_{GS} = 10V$ | Steady State | $T_A = 25^\circ C$ | I_D | 400 | mA |
| | | $T_A = 70^\circ C$ | | 310 | |

Thermal Characteristics

| Characteristic | Symbol | Value | Units |
|---|------------------|-------------|--------------|
| Power Dissipation, @ $T_A = 25^\circ C$ (Note 4) | P_D | 430 | mW |
| Thermal Resistance, Junction to Ambient @ $T_A = 25^\circ C$ (Note 4) | $R_{\theta JA}$ | 290 | $^\circ C/W$ |
| Power Dissipation, @ $T_A = 25^\circ C$ (Note 5) | P_D | 840 | mW |
| Thermal Resistance, Junction to Ambient @ $T_A = 25^\circ C$ (Note 5) | $R_{\theta JSA}$ | 147 | $^\circ C/W$ |
| Operating and Storage Temperature Range | T_J, T_{STG} | -55 to +150 | $^\circ C$ |

Electrical Characteristics @ $T_A = 25^\circ C$ unless otherwise specified

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|--|--------------|-----|--------|----------|----------|---|
| OFF CHARACTERISTICS (Note 6) | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | 60 | - | - | V | $V_{GS} = 0V, I_D = 250\mu A$ |
| Zero Gate Voltage Drain Current $T_J = 25^\circ C$ | I_{DSS} | - | - | 0.1 | μA | $V_{DS} = 60V, V_{GS} = 0V$ |
| Gate-Body Leakage | I_{GSS} | - | - | ± 10 | μA | $V_{GS} = \pm 20V, V_{DS} = 0V$ |
| ON CHARACTERISTICS (Note 6) | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | 1.2 | - | 2.0 | V | $V_{DS} = V_{GS}, I_D = 250\mu A$ |
| Static Drain-Source On-Resistance | $R_{DS(ON)}$ | - | - | 3.0 | Ω | $V_{GS} = 10V, I_D = 0.115A$ $V_{GS} = 5V, I_D = 0.1115A$ |
| | | | | 4.0 | | |
| Forward Transfer Admittance | $ Y_{fs} $ | 80 | 320 | - | mS | $V_{DS} = 10V, I_D = 0.115A$ |
| Diode Forward Voltage | V_{SD} | - | 0.7 | 1.2 | V | $V_{GS} = 0V, I_S = 0.115A$ |
| DYNAMIC CHARACTERISTICS (Note 7) | | | | | | |
| Input Capacitance | C_{iss} | - | 25 | - | pF | $V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$ $V_{DD} = 30V, V_{GEN} = 10V,$ $R_{GEN} = 25\Omega, I_D = 0.115A$ |
| Output Capacitance | C_{oss} | - | 4.7 | - | pF | |
| Reverse Transfer Capacitance | C_{rss} | - | 2.5 | - | pF | |
| Turn-On Delay Time | $t_{D(on)}$ | - | 3.27 | - | ns | |
| Turn-On Rise Time | t_r | - | 3.15 | - | ns | |
| Turn-Off Delay Time | $t_{D(off)}$ | - | 12.025 | - | ns | |
| Turn-Off Fall Time | t_f | - | 6.29 | - | ns | |

- Notes:
4. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
 5. Device mounted on 2" x 2" FR-4 PCB with high coverage 2 oz. Copper, single sided.
 6. Short duration pulse test used to minimize self-heating effect.
 7. Guaranteed by design. Not subject to production testing.

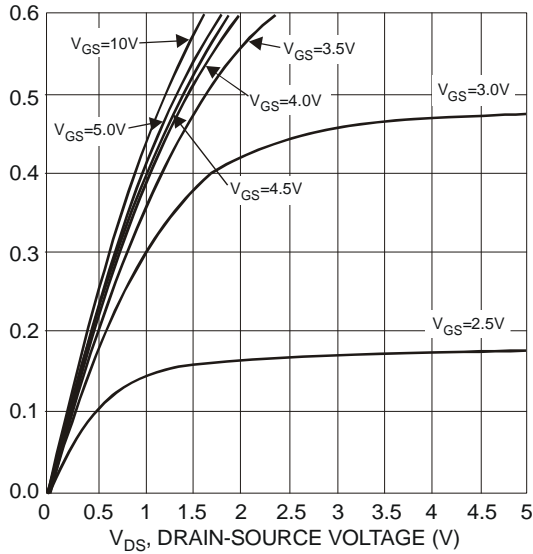


Fig. 1 Typical Output Characteristics

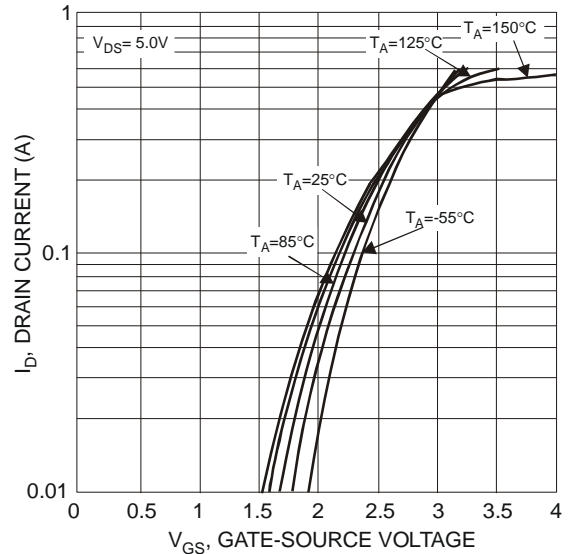


Fig. 2 Typical Transfer Characteristics

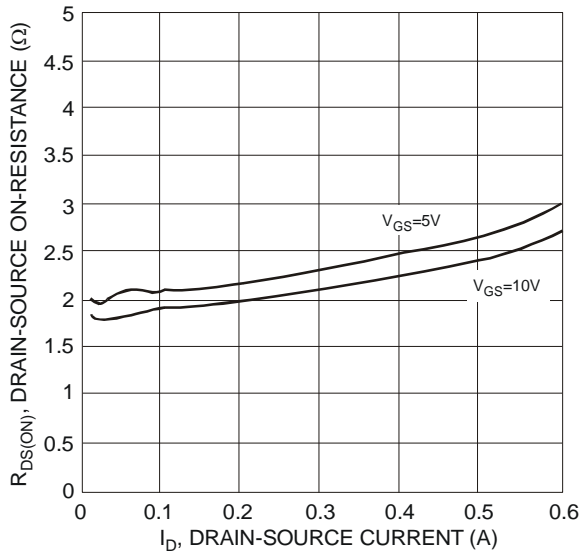


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Charge

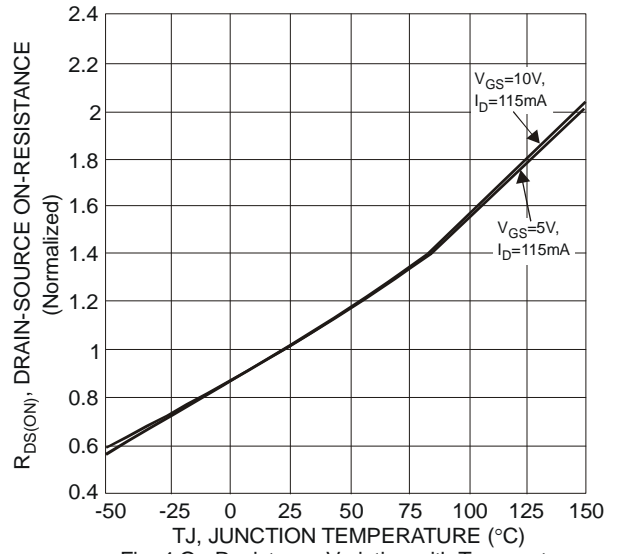


Fig. 4 On-Resistance Variation with Temperature

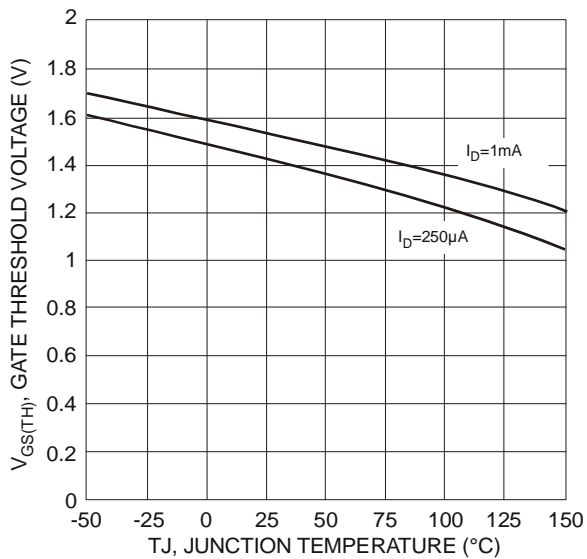


Fig. 5 Gate Threshold Variation vs. Ambient Temperature

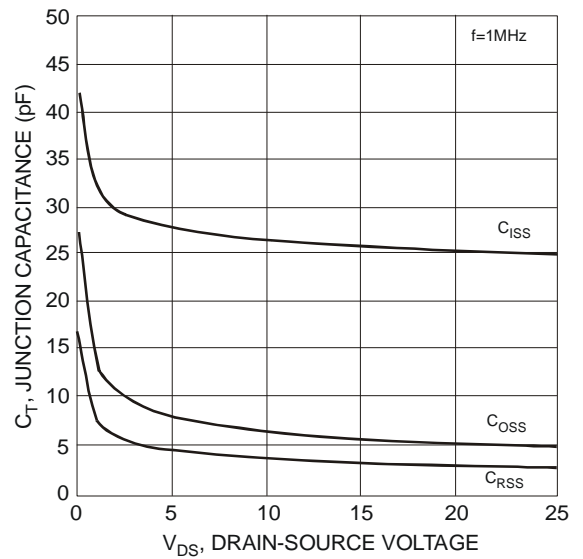


Fig. 6 Typical Junction Capacitance

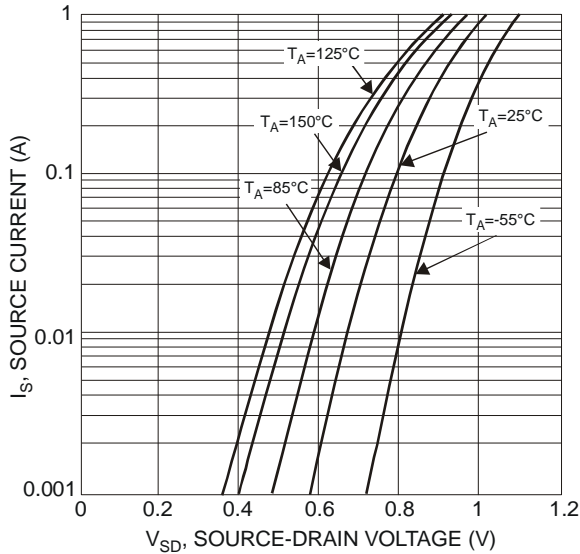
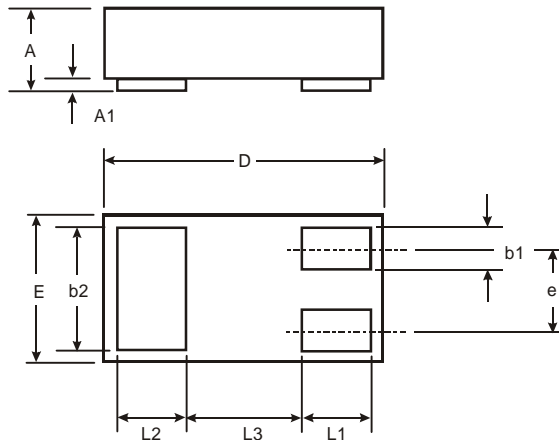


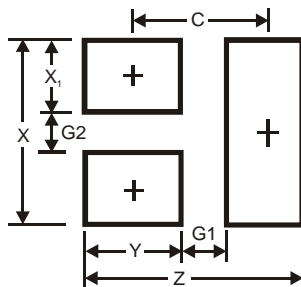
Fig. 7 Diode Forward Voltage vs. Current

Package Outline Dimensions



| X1-DFN1006-3 | | | |
|----------------------|------|-------|------|
| Dim | Min | Max | Typ |
| A | 0.47 | 0.53 | 0.50 |
| A1 | 0 | 0.05 | 0.03 |
| b1 | 0.10 | 0.20 | 0.15 |
| b2 | 0.45 | 0.55 | 0.50 |
| D | 0.95 | 1.075 | 1.00 |
| E | 0.55 | 0.675 | 0.60 |
| e | — | — | 0.35 |
| L1 | 0.20 | 0.30 | 0.25 |
| L2 | 0.20 | 0.30 | 0.25 |
| L3 | — | — | 0.40 |
| All Dimensions in mm | | | |

Suggested Pad Layout



| Dimensions | Value (in mm) |
|------------|---------------|
| Z | 1.1 |
| G1 | 0.3 |
| G2 | 0.2 |
| X | 0.7 |
| X1 | 0.25 |
| Y | 0.4 |
| C | 0.7 |

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